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Fax Cover Sheet

DATE:	November 16, 2002	PAGES:	<u>3 (three) w/cover</u>
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Message

DOCKET GS150

Please see attached: Response to Restriction Requirement

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Iuan Hshich et al.
Serial No.: 10/010,484
Filed: November 20, 2001
Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure
Art Unit: 2826
Examiner: Tan N. Tran
Docket No.: GS 150

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Assistant Commissioner for Patents
Washington, D.C. 20231

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RESPONSE TO RESTRICTION REQUIREMENT

Sir:

In response to the Office Action dated October 18, 2002, kindly consider the following response to the outstanding restriction requirement.

REMARKS

Claims 1-21 are pending in the application. Restriction was required to the following allegedly distinct inventions:

I. Claims 1-16, drawn to a semiconductor device, classified in class 257, subclass 330.

II. Claims 17-21, drawn to a method of manufacturing a semiconductor device, classified in class 438, subclass 259.

The Office Action indicates that the inventions are distinct because "the device of the group I invention could be made by a process materially different than that of the group II invention".